TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

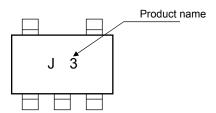
# TC7SZ02F,TC7SZ02FU

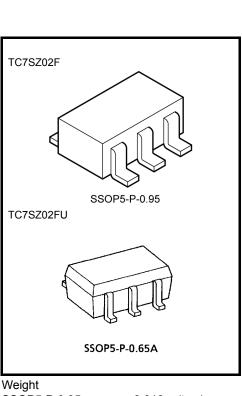
#### 2 Input NOR Gate

#### Features

- High output drive: ±24 mA (min) at V<sub>CC</sub> = 3 V
- Super high speed operation: tpd=2.4 ns (typ.)
  - at V<sub>CC</sub> = 5 V, 50 pF
- Operation voltage range: V<sub>CC (opr)</sub> = 1.8~5.5 V
- 5.5-V tolerant inputs
- 5.5-V power down protection output
- Matches the performance of TC74LCX series when operated at 3.3- V  $\mathsf{V}_{CC}$

### Marking





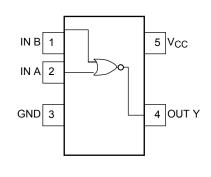
SSOP5-P-0.95 : 0.0 SSOP5-P-0.65A : 0.0

#### : 0.016 g (typ.) : 0.006 g (typ.)

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V <sub>CC</sub>	-0.5~6	V
DC input voltage	V <sub>IN</sub>	-0.5~6	V
DC output voltage	V <sub>OUT</sub>	-0.5~6	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	I <sub>OK</sub>	-20	mA
DC output current	IOUT	±50	mA
DC V <sub>CC</sub> /ground current	ICC	±50	mA
Power dissipation	PD	200	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C
Lead temperature (10s)	ΤL	260	°C

### Pin Assignment (top view)



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

# <u>TOSHIBA</u>

### Logic Diagram



### Truth Table

Inp	out	Output
А	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

### **Operating Ranges**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	1.8~5.5	V
		1.5~5.5 (Note 1)	v
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~5.5 (Note 2)	V
		0~V <sub>CC</sub> (Note 3)	v
Operating temperature	T <sub>opr</sub>	-40~85	°C
	dt/dv	0~20 (V_{CC} = 1.8 V, 2.5 V $\pm$ 0.2 V)	ns/V
Input rise and fall time		0~10 (V_{CC} = 3.3 V $\pm$ 0.3 V)	
		0~5 (V <sub>CC</sub> = 5.5 V $\pm$ 0.5 V)	

Note 1: Data retention only

Note 2:  $V_{CC} = 0 V$ 

Note 3: High or Low state

### **Electrical Characteristics**

### **DC Characteristics**

Characteristics Symbol Test Co		at Condition	Condition		Ta = 25°C			Ta = -40~85°C		
		V <sub>CC</sub> (V)		Min	Тур.	Max	Min	Max	Unit	
High-level input VIH —			1.8	V <sub>CC</sub> × 0.88	_	_	V <sub>CC</sub> × 0.88	_	v	
voltage		_	2.3~5.5	V <sub>CC</sub> × 0.75	_	_	V <sub>CC</sub> × 0.75	_	v	
Low-level input VIL —		1.8	_	_	V <sub>CC</sub> × 0.12	_	V <sub>CC</sub> × 0.12	v		
		_	2.3~5.5	_	_	V <sub>CC</sub> × 0.25	_	V <sub>CC</sub> × 0.25	V	
				1.8	1.7	1.8	_	1.7		
			I <sub>OH</sub> = –100 μA	2.3	2.2	2.3		2.2		V
			10Η = -100 μΛ	3.0	2.9	3.0		2.9		
High-level	Vон	V <sub>IN</sub> = V <sub>IL</sub>		4.5	4.4	4.5		4.4		
output voltage	∨ОН	VIN – VIL	$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.15	_	1.9	_	
			I <sub>OH</sub> = -16 mA	3.0	2.4	2.8		2.4		
			I <sub>OH</sub> = -24 mA	3.0	2.3	2.68		2.3		
			I <sub>OH</sub> = -32 mA	4.5	3.8	4.2		3.8		
		VIN = VIH or VIL	I <sub>OL</sub> = 100 μA	1.8		0	0.1		0.1	v
				2.3		0	0.1		0.1	
				3.0		0	0.1		0.1	
Low-level	Ve			4.5		0	0.1		0.1	
output voltage	VOL		I <sub>OL</sub> = 8 mA	2.3	_	0.1	0.3	_	0.3	
			I <sub>OL</sub> = 16 mA	3.0	_	0.15	0.4	_	0.4	
			I <sub>OL</sub> = 24 mA	3.0	_	0.22	0.55	_	0.55	
			I <sub>OL</sub> = 32 mA	4.5	_	0.22	0.55	_	0.55	
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V	V <sub>IN</sub> = 5.5 V or GND			_	±1	_	±10	μA
Power off leakage current	IOFF	$V_{IN}$ or $V_{OUT} = 5.5 V$		0.0			1		10	μA
Quiescent supply current	ICC	$V_{IN} = V_{CC}$	$V_{IN} = V_{CC}$ or GND		_	_	2	_	20	μA

### AC Characteristics (unless otherwise specified, Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = −40~85°C		Unit	
Characteristics	Symbol		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
Propagation delay time	<sup>t</sup> pLH tpHL	$C_L = 15 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	1.8	2.0	4.4	9.5	2.0	10.0	- ns
			$2.5\pm0.2$	0.8	2.9	6.5	0.8	7.0	
			$\textbf{3.3}\pm\textbf{0.3}$	0.5	2.3	4.5	0.5	4.7	
			$5.0\pm0.5$	0.5	1.9	3.9	0.5	4.1	
		$C_L = 50 \text{ pF},$ $R_L = 500 \Omega$	$\textbf{3.3}\pm\textbf{0.3}$	1.5	2.9	5.0	1.5	5.2	
			$5.0\pm0.5$	0.8	2.4	4.3	0.8	4.5	
Input capacitance	C <sub>IN</sub>	_	0~5.5	_	4	_	_	_	pF
Power dissipation capacitance	6	(Note 4)	3.3	_	23		_	_	nΕ
	C <sub>PD</sub>		5.5	_	30		_	_	рF

Note 4: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

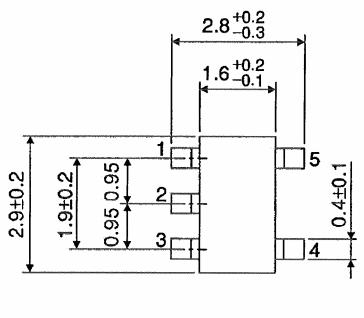
 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

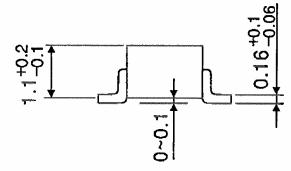
# <u>TOSHIBA</u>

### Package Dimensions

SSOP5-P-0.95

Unit : mm

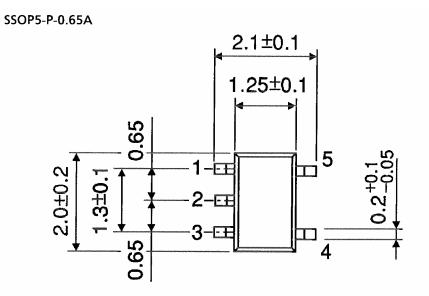


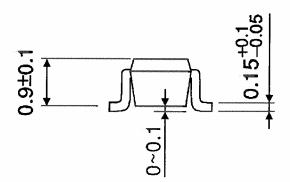


Weight: 0.016 g (typ.)

# <u>TOSHIBA</u>

### Package Dimensions





Weight: 0.006 g (typ.)

Unit : mm

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20070701-EN GENERAL

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